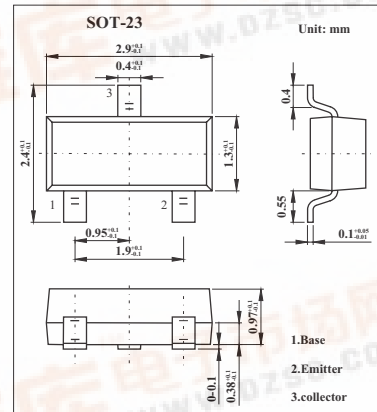


SMD Type Transistors

Silicon PNP Epitaxial Planar Type
2SA1035



Features

- Low noise voltage NV.
- High forward current transfer ratio hFE.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-55	V
Collector-emitter voltage	V _{CEO}	-55	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _C	-50	mA
Peak collector current	I _{CP}	-100	mA
Collector power dissipation	P _C	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V _{CB0}	I _C = -10 μA, I _E = 0	-55			V
Collector-emitter voltage	V _{CEO}	I _C = -2 mA, I _B = 0	-55			V
Emitter-base voltage	V _{EB0}	I _E = -10 μA, I _C = 0	-5			V
Base-emitter voltage *	V _{BE}	V _{CE} = -1 V, I _C = -100 mA		-0.7	-1.0	V
Collector-base cutoff current	I _{CB0}	V _{CB} = -10 V, I _E = 0			-0.1	μA
Collector-emitter cutoff current	I _{CEO}	V _{CE} = -10 V, I _B = 0			-1	μA
Forward current transfer ratio	h _{FE}	V _{CE} = -5 V, I _C = -2 mA	180		700	
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = -100 mA, I _B = -10 mA			-0.6	V
Transition frequency	f _T	V _{CB} = -5 V, I _E = 2 mA, f = 200 MHz		200		MHz
Noise voltage	NV	V _{CE} = -10 V, I _C = -1 mA, G _v = 80 dB R _g = 100 kΩ, F _{unction} = FLAT			150	mV

* Pulse measurement.

hFE Classification

Marking	HR	HS	HT
hFE	180~360	260~520	360~700

